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## Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

## Listing of Claims:

Claims 1-16 (Canceled)

17. (Currently Amended) Light emitting semiconductor body for use in an LED housing,
said semiconductor body being provided with a layer comprising a wavelengthconverting casting composition; and

said casting composition comprising luminous substance particles;

said luminous substance particles comprising luminous substance pigments selected from the group consisting of garnets doped with rare earths; thiogallates doped with rare earths; aluminates doped with rare earths; and orthohsilicates doped with rare earths; and

said luminous substance pigments having grain sizes  $\leq 20~\mu m$  and a mean grain diameter  $d_{50}$  a median diameter  $\leq 5~\mu m$ , wherein 50% of the pigments have a grain diameter greater than said median diameter and 50% of the pigments have a grain diameter less than said median diameter.

- 18. Canceled.
- 19. Canceled.

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20. (Currently Amended) Semiconductor body according to claim 17, wherein the median diameter mean grain diameter d<sub>50</sub> of said luminous substance pigments is between 1 and 2 micrometers.

- 21. (Previously Presented) Semiconductor body according to claim 17, wherein said luminous substance pigments contain Ce-doped garnet material.
- 22. (Previously Presented) Semiconductor body according to claim 17, wherein said luminous substance pigments contain YAG:Ce material.
- 23. (Previously Presented) Semiconductor body according to claim 17, wherein the iron content in the casting composition is ≤20 ppm.
- 24. (Previously Presented) Semiconductor body according to claim 17, wherein the luminous substance pigments are provided with a silicone coating.
- 25. (Previously Presented) Semiconductor body according to claim 17, wherein said luminous substance pigments convert radiation from the ultraviolet, blue or green spectral range into light with a relatively longer wavelength.
- 26. (Previously Presented) Semiconductor body according to claim 17, wherein said layer containing light-scattering particles.
- 27. (Previously Presented) Semiconductor body according to claim 17, wherein said semiconductor body is adapted to emit radiation in a blue spectral range having a maximum luminescence intensity at a wavelength between 420 nm and 460 nm.
- 28. (Currently Amended) Light emitting semiconductor body for use in an LED housing,

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said semiconductor body being provided with a layer comprising a wavelength-converting casting composition; and

said casting composition comprising luminous substance particles;

said luminous substance particles comprising luminous substance pigments from Ce-doped phosphors; and

said luminous substance pigments having grain sizes  $\leq$  20  $\mu$ m and a mean grain diameter  $d_{50}$  a median diameter  $\leq$  5  $\mu$ m, wherein 50% of the pigments have a grain diameter greater than said median diameter and 50% of the pigments have a grain diameter less than said median diameter.

- 29. Canceled.
- 30. Canceled.
- 31. (Currently Amended) Semiconductor body according to claim 28, wherein the median diameter mean grain diameter d<sub>50</sub> of said luminous substance pigments is between 1 and 2 micrometers.
- 32. (Previously Presented) Semiconductor body according to claim 28, wherein the iron content in the casting composition is ≤20 ppm.
- 33. (Previously Presented) Semiconductor body according to claim 28, wherein the luminous substance pigments are provided with a silicone coating.
- 34. (Previously Presented) Semiconductor body according to claim 28, wherein said luminous substance pigments convert radiation from the ultraviolet, blue or green spectral range into light with a relatively longer wavelength.

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35. (Previously Presented) Semiconductor body according to claim 28, wherein said layer containing light-scattering particles.

- 36. (Previously Presented) Semiconductor body according to claim 28, wherein said semiconductor body is adapted to emit radiation in a blue spectral range having a maximum luminescence intensity at a wavelength between 420 nm and 460 nm.
- 37. (Previously Presented) Semiconductor body according to claim 17, wherein the casting composition further comprises a transparent resin.
- 38. (Previously Presented) Semiconductor body according to claim 37, wherein the transparent resin is an epoxy resin.
- 39. (Previously Presented) Semiconductor body according to claim 28, wherein the casting composition further comprises a transparent resin.
- 40. (Previously Presented) Semiconductor body according to claim 39, wherein the transparent resin is an epoxy resin.